

Silicon NPN Power Transistors

2SD1880

DESCRIPTION

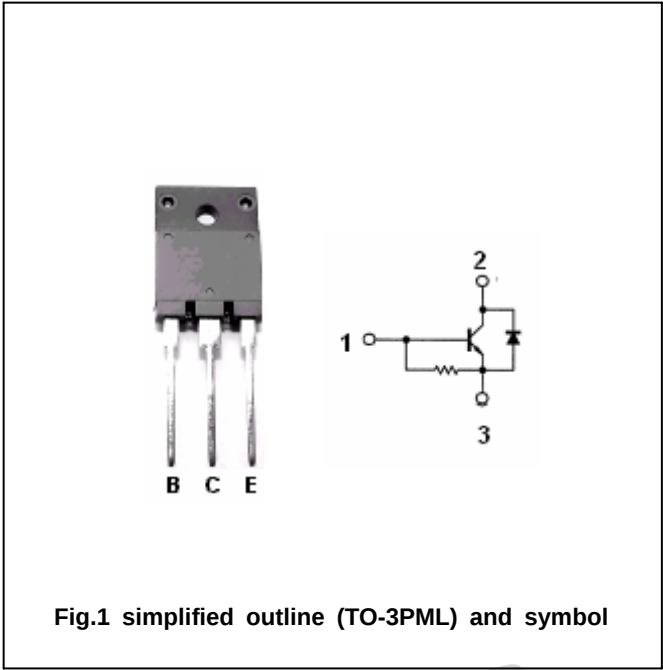
- With TO-3PML package
- High speed
- High breakdown voltage
- High reliability
- Built in damper diode

APPLICATIONS

- Color TV horizontal deflection output
- Color display horizontal deflection output.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		30	A
P_C	Collector power dissipation		70	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

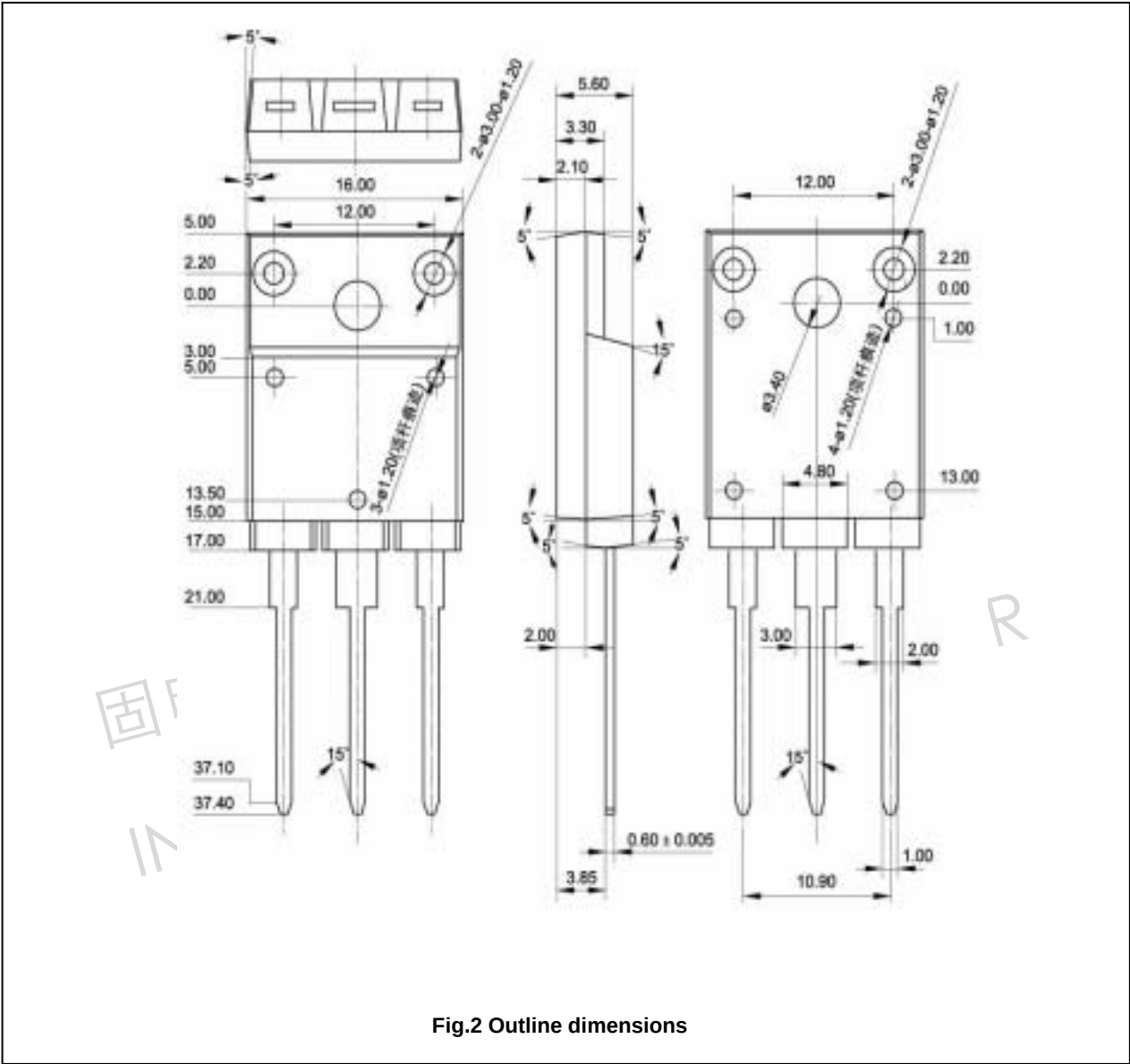
Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA ; I_B=0$	800			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A ; I_B=1.2A$			5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=6A ; I_B=1.2A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800V ; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=4V ; I_C=0$	40		130	mA
I_{CES}	Collector cut-off current	$V_{CE}=1500V$			1.0	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=5V$	8			
h_{FE-2}	DC current gain	$I_C=6A ; V_{CE}=5V$	5		10	
V_F	Diode forward voltage	$I_{EC}=8A$			2	V
t_f	Fall time	$I_C=6A ; R_L=33.3\Omega$ $I_{B1}=1.2A ; I_{B2}=-2.4A ; V_{CC}=200V$		0.1	0.3	μs

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PACKAGE OUTLINE



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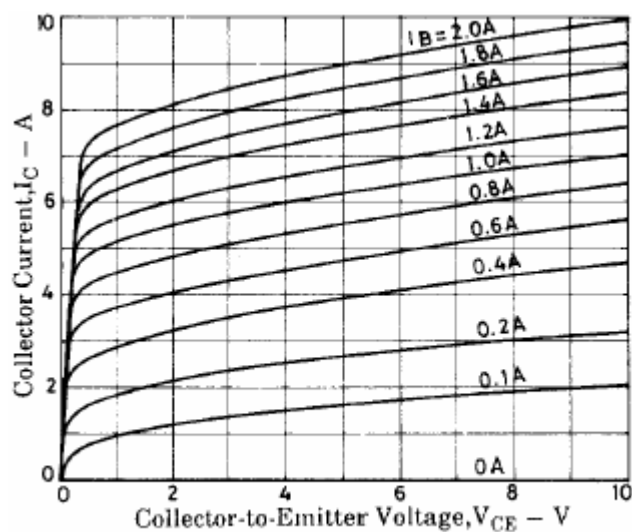


Fig.3 Static Characteristic

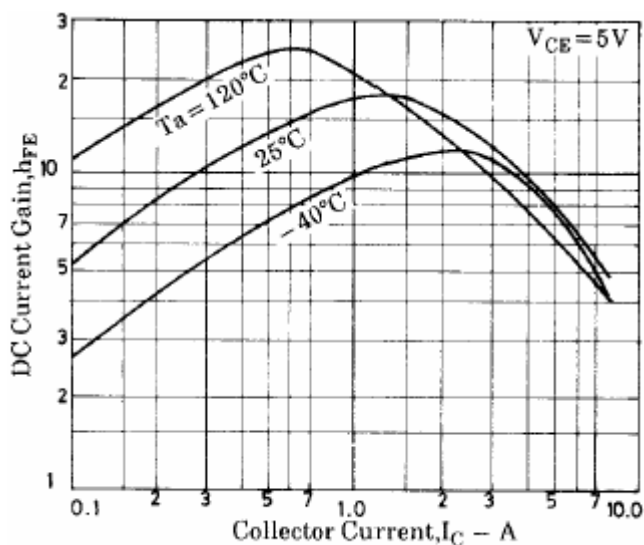


Fig.4 DC current Gain

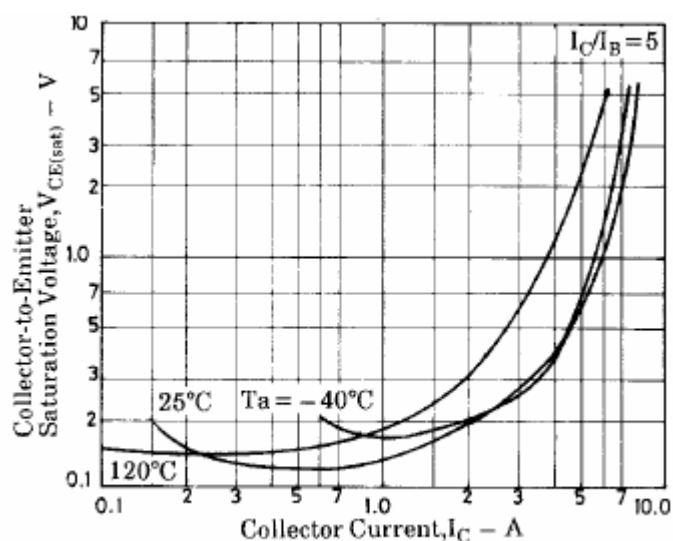


Fig.5 Collector-Emitter Saturation Voltage

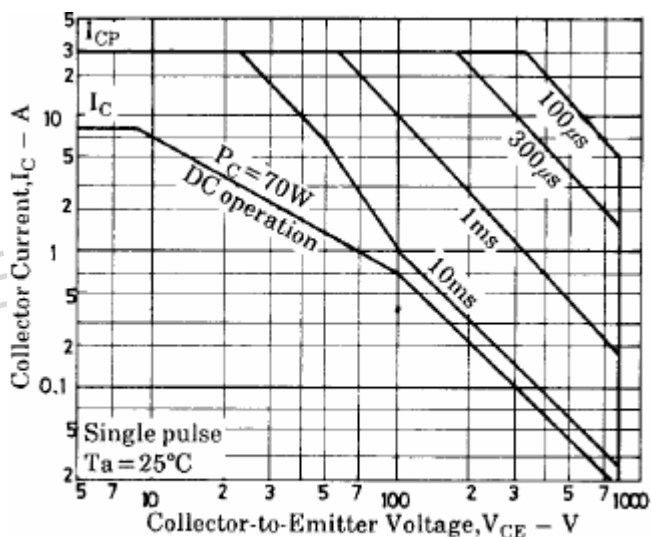


Fig.6 Safe Operating Area